

IN THE SPECIFICATION

Please amend the Title at page 1, line 1 to read:

METHOD OF FABRICATING A SEMICONDUCTOR DEVICE INCLUDING A
DIELECTRIC LAYER FORMED USING A REACTIVE AGENT

Please amend the Abstract at page 18, lines 2-9 to read:

A method of fabricating a semiconductor device ~~Semiconductor devices that utilize~~
including a silicon-containing dielectric layer is provided ~~are disclosed~~. In one embodiment, a silicon-containing material is deposited on a substrate. The deposited material is processed with a reactive agent to react with silicon atoms of the deposited material to form the dielectric layer. The silicon-containing dielectric layer provides for improved or smaller semiconductor devices by reducing leakage and increasing the dielectric constant.